

coupling a chuck to a pedestal;

coupling the wafer to the chuck;

rotating the pedestal; and

plasma etching the wafer while the pedestal is rotating.

Brend

11. (Amended) The method of claim 10 further comprising the step of internally cooling the chuck.

8/16/2002 Sch 1/5. 15. (Amended) The method of claim 10 further comprising the step of initializing process parameters, the process parameters comprising gas flow, process chamber pressure, wafer temperature, and pedestal rotation speed.

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Please add the following new claim:

26. (New) A method of plasma etching a wafer by means of a plasma etching machine comprising a process chamber, a rotatable, internally cooled chuck disposed in the process chamber, a clamp coupled to the chuck; a controller coupled to the process chamber and chuck for controlling gas flow and pressure in the process chamber and rotation of the chuck, a pedestal coupled to the chuck and cooperating therewith to define a coolant chamber, the pedestal including a coolant passage in fluid communication with a coolant source and the coolant chamber; and a lift actuator coupled to the coolant passage, the coolant passage moving in the pedestal in response to actuation of the lift mechanism to lift the wafer from the chuck, said method comprising the steps of:

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